

T-46-13-15

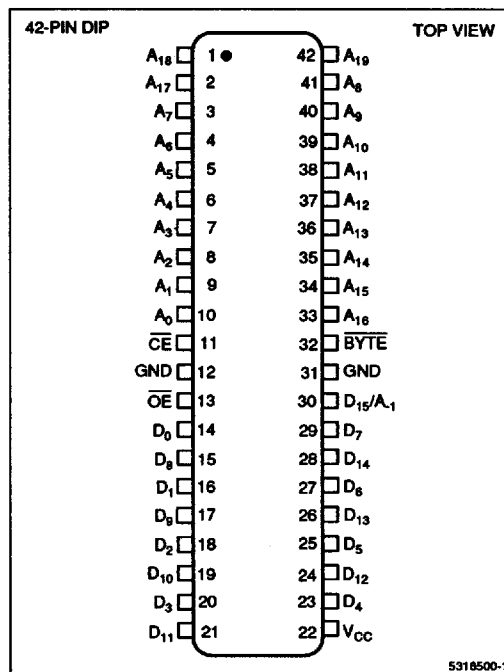
LH5316500

**CMOS 16M (2M × 8 / 1M × 16)
Mask-Programmable ROM**

FEATURES

- 2,097,152 × 8 bit organization
(Byte mode: $\overline{\text{BYTE}} = V_{IL}$)
1,048,576 × 16 bit organization
(Word mode: $\overline{\text{BYTE}} = V_{IH}$)
- Access time: 150 ns (MAX.)
- Power consumption:
Operating: 50 mA (MAX.)
Standby: 100 μ A (MAX.)
- Fully static operation
- TTL compatible I/O
- Three-state outputs
- Single +5 V power supply
- Packages:
42-pin, 600-mil DIP *
44-pin, 600-mil SOP
48-pin, 12 × 18 TSOP I
64-pin, 14 × 20 mm² QFP

PIN CONNECTIONS

**Figure 1. Pin Connections for DIP Package**

DESCRIPTION

The LH5316500 is a 16M-bit mask-programmable ROM organized as 2,097,152 × 8 bits (Byte mode) or 1,048,576 × 16 bits (Word mode) that can be selected by a $\overline{\text{BYTE}}$ input pin. It is fabricated using silicon-gate CMOS process technology.

It provides high density and high speed access in a variety of packages including small and thin surface mount technology.

* NOTE: For the 42-pin DIP, pin 30 becomes LSB address input (A₁) when in byte mode, and data output (D₁₅) when in word mode.

CMOS 16M (2M × 8 / 1M × 16)
Mask-Programmable ROM

LH5316500

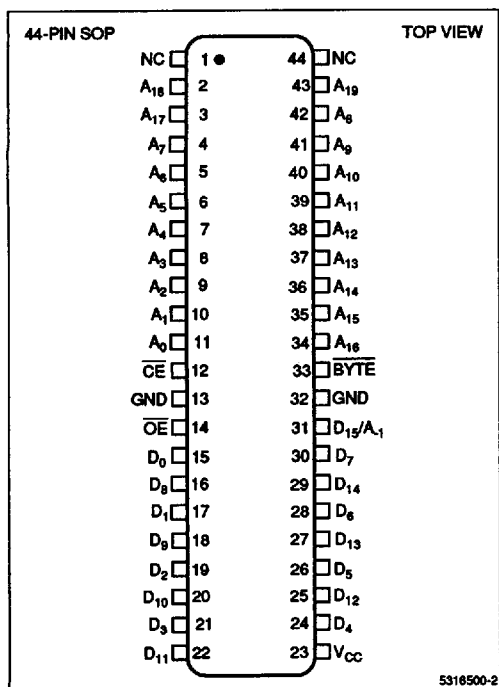


Figure 2. Pin Connections for SOP Package

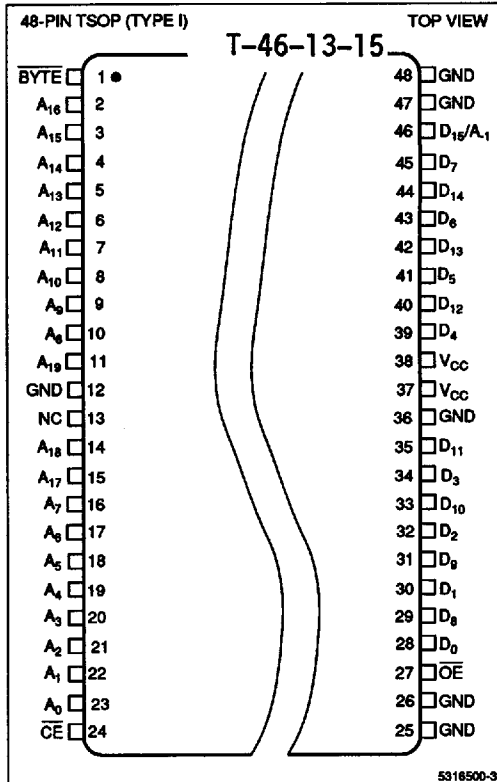


Figure 3. Pin Connections for TSOP Package (Type I)

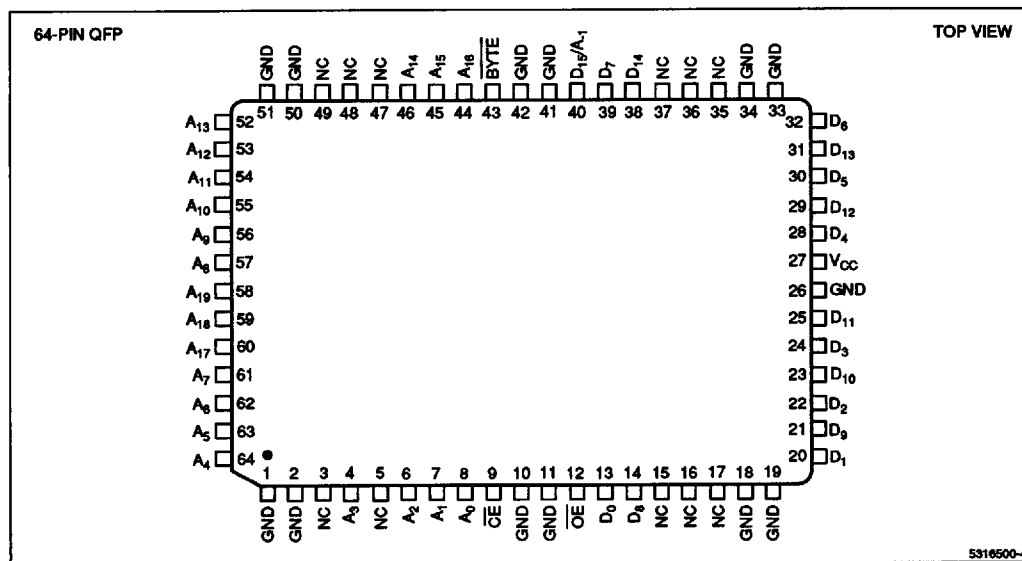
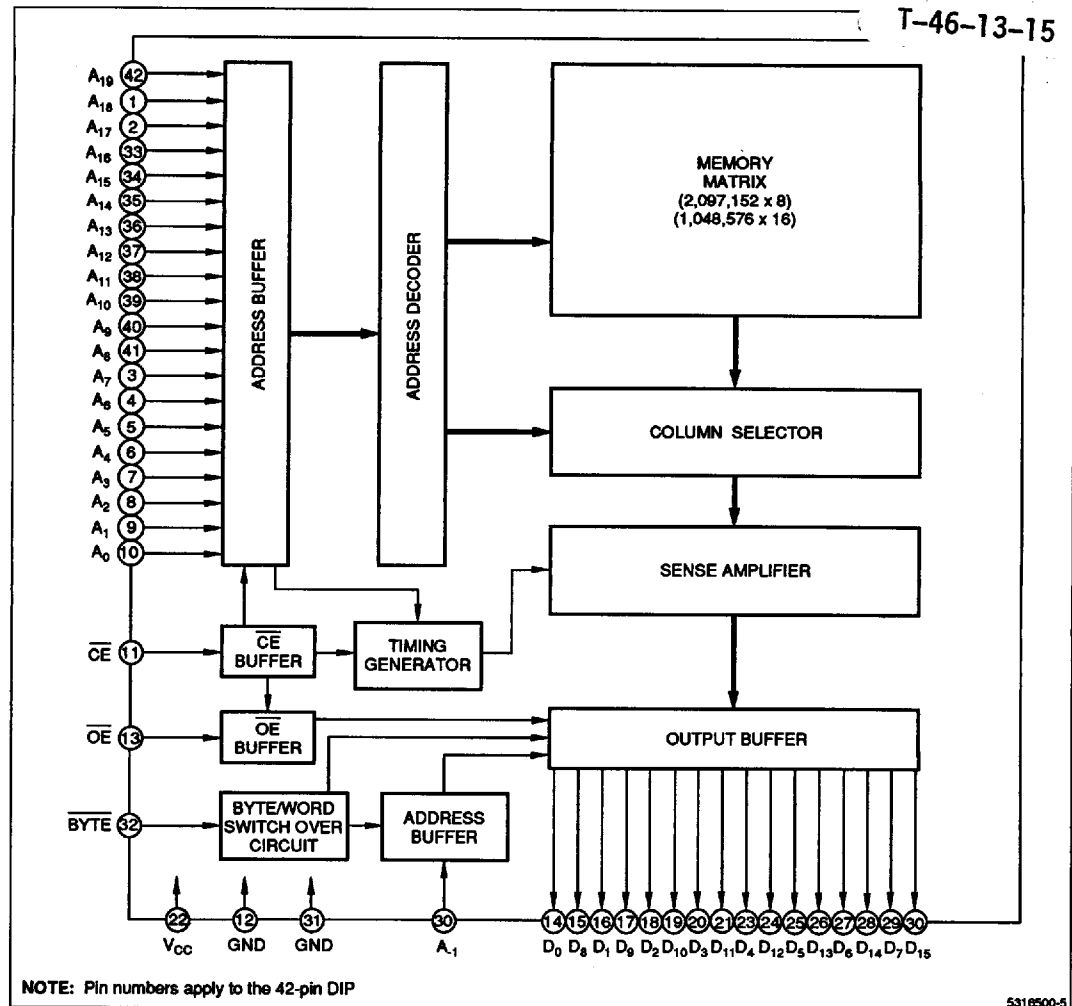


Figure 4. Pin Connections for QFP Package

T-46-13-15



5316500-5

Figure 5. LH5316500 Block Diagram

PIN DESCRIPTION

SIGNAL	PIN NAME
A ₁ - A ₁₉	Address Input
D ₀ - D ₁₅	Data output
BYTE	8/16-bit (Byte/Word) mode switch Input
$\overline{CE}$	Chip Enable Input

SIGNAL	PIN NAME
$\overline{OE}$	Output Enable Input
V _{cc}	Power supply (+5 V)
GND	Ground
NC	No Connection

LH5316500

TRUTH TABLE

T-46-13-15

$\overline{CE}$	$\overline{OE}$	BYTE	A ₁ (D ₁₅)	DATA OUTPUT		MODE	ADDRESS INPUT		SUPPLY CURRENT
				D ₀ - D ₇	D ₈ - D ₁₅		LSB	MSB	
H	X	X	X	High-Z	High-Z	High-Z	—	—	Standby
L	H	X	X	High-Z	High-Z		—	—	Operating
L	L	H	Inhibit	D ₀ - D ₇	D ₈ - D ₁₅	16-Bit	A ₀	A ₁₉	Operating
L	L	L	L	D ₀ - D ₇	High-Z	8-Bit	A ₁	A ₁₉	Operating
L	L	L	H	D ₈ - D ₁₅	High-Z	8-Bit	A ₁	A ₁₉	Operating

NOTE:

X = Don't Care; High-Z = High-Impedance

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Supply voltage	V _{CC}	-0.3 to +7.0	V
Input voltage	V _{IN}	-0.3 to V _{CC} + 0.3	V
Output voltage	V _{OUT}	-0.3 to V _{CC} + 0.3	V
Operating temperature	T _{opr}	0 to +70	°C
Storage temperature	T _{stg}	-55 to +150	°C

RECOMMENDED OPERATING CONDITIONS (T_A = 0 to +70°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply voltage	V _{CC}	4.5	5.0	5.5	V

DC CHARACTERISTICS (V_{CC} = 5 V ± 10%, T_A = 0 to +70°C)

PARAMETER	SYMBOL	CONDITIONS	MIN.	MAX.	UNIT	NOTE
Input "High" voltage	V _{IH}		2.2	V _{CC} + 0.3	V	
Input "Low" voltage	V _{IL}		-0.3	0.8	V	
Output "High" voltage	V _{OH}	I _{OH} = -400 μA	2.4		V	
Output "Low" voltage	V _{OL}	I _{OL} = 2.0 mA		0.4	V	
Input leakage current	I _I	V _{IN} = 0 V, V _{CC}		10	μA	
Output leakage current	I _{LO}	V _{OUT} = 0 V, V _{CC}		10	μA	1
Operating current	I _{CC1}	t _{RC} = 150 ns		50	mA	2
	I _{CC2}	t _{RC} = 1 μs		40		
Standby current	I _{SB1}	$\overline{CE}$ = V _{IH}		2	mA	
	I _{SB2}	$\overline{CE}$ = V _{CC} - 0.2 V		100		
Input capacitance	C _{IN}	f = 1 MHz, T _A = 25°C		10	pF	
Output capacitance	C _{OUT}			10	pF	

NOTES:

1. $\overline{CE}$ = V_{IH}, $\overline{OE}$ = V_{IH} (Outputs open).
2. V_{IN} = V_{IH}/V_{IL}, $\overline{CE}$ = V_{IL} (TTL level).

CMOS 16M (2M × 8 / 1M × 16)

Mask-Programmable ROM

LH5316500

AC CHARACTERISTICS ($V_{CC} = 5\text{ V} \pm 10\%$, $T_A = 0\text{ to }+70^\circ\text{C}$)

T-46-13-15

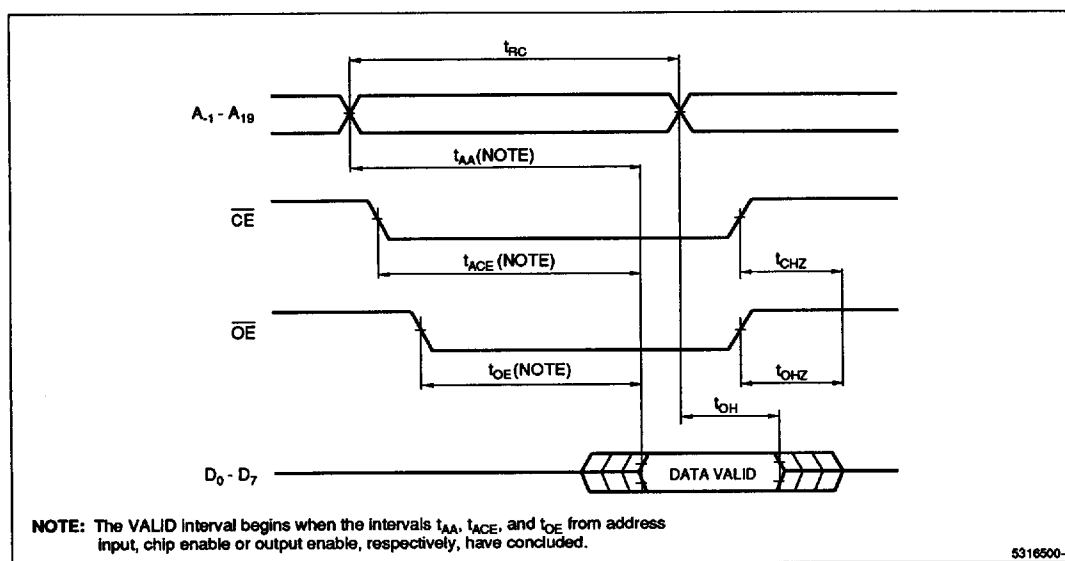
PARAMETER	SYMBOL	MIN.	MAX.	UNIT	NOTE
Read cycle time	t_{RC}	150		ns	
Address access time	t_{AA}		150	ns	
Chip enable access time	t_{ACE}		150	ns	
Output enable time	t_{OE}		70	ns	
Output hold time	t_{OH}	5		ns	
Output floating time	t_{CHZ}		60	ns	1
	t_{OHZ}				

NOTE:

1. Determined by the time for the output to be opened, irrespective of output voltage.

AC TEST CONDITIONS

PARAMETER	RATING
Input voltage amplitude	0.6 V to 2.4 V
Input rise/fall time	10 ns
Input reference level	1.5 V
Output reference level	0.8 V, 2.2 V
Output load condition	1TTL + 100 pF

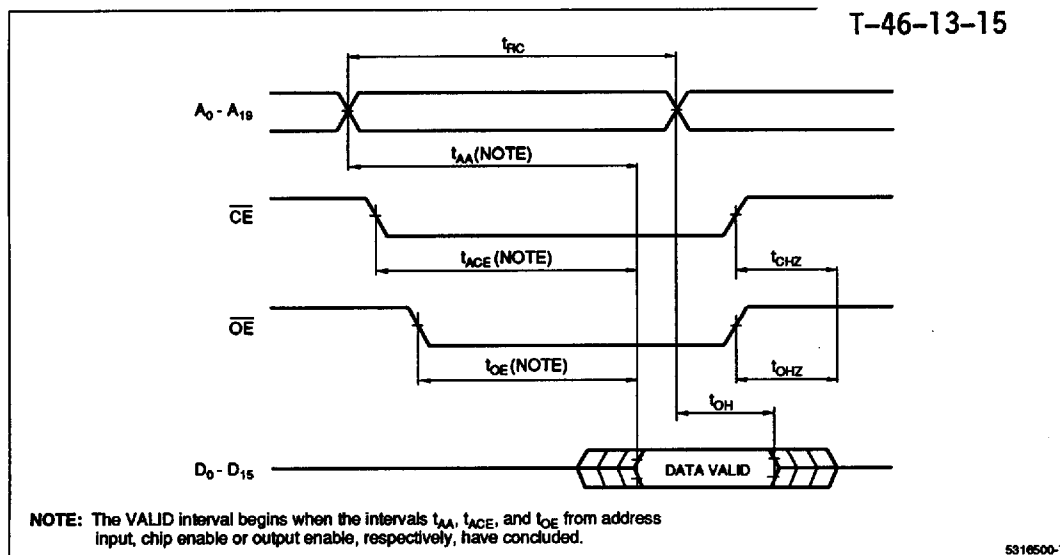


5316500-6

Figure 6. $\overline{\text{BYTE}} = \text{VIL}$ in Byte Mode

LH5316500

T-46-13-15



5316500-7

Figure 7. $\overline{\text{BYTE}} = V_{IH}$ in Word Mode

ORDERING INFORMATION

LH5316500 Device Type	X Package	-## Speed	
		15 150	Access Time (ns)
			- D 42-pin, 600-mil DIP (DIP42-P-600) - N 44-pin, 600-mil SOP (SOP44-P-600) - M 64-pin, 14 x 20 mm² QFP (QFP64-P-1420) - T 48-pin, 12 x 18 mm² TSOP (TSOP48-P-1218)
			CMOS 16M (2M x 8 OR 1M x 16) Mask Programmable ROM

Example: LH5316500D-15 (CMOS 16M (2M x 8) Mask-Programmable ROM, 150 ns, 42-pin, 600-mil DIP)

5316500-8